

BD680

Silicon PNP Transistors



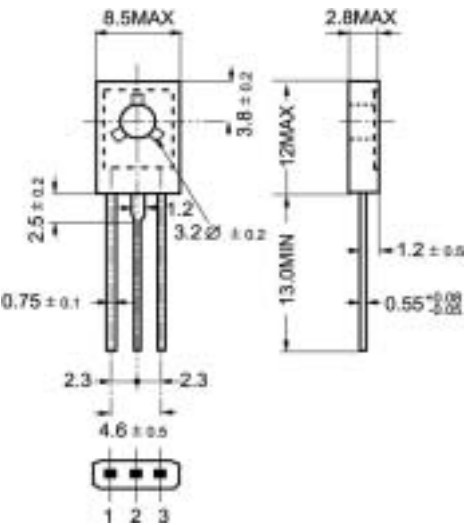
ECB

◆ Features

- With TO-126 package
- In monolithic Darlington configuration
- This transistor is intended for use in medium power linear and switching applications
- Complement to type BD679

◆ Absolute Maximum Ratings Tc=25℃

SYMBOL	PARAMETER	RATING	UNIT
V _{CBO}	Collector to base voltage	80	V
V _{CEO}	Collector to emitter voltage	80	V
V _{CER}	Emitter to base voltage		
V _{EB}	Emitter to base voltage	5	V
I _B	Base Current		
I _C	Collector current-Continuous	4	A
P _D	Total Power Dissipation@TC=25℃	40	W
T _j	Junction temperature	150	℃
T _{stg}	Storage temperature	-55~150	℃



TO-126

◆ Electrical Characteristics Tc=25℃

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C =50mA; I _B =0	80		V
V _{CBO}	Collector-Base Voltage				
I _{CEO}	Collector Cutoff Current	V _{CE} =40V; I _B =0		500	uA
I _{CBO}	Collector Cutoff Current	V _{CB} =80V; I _E =0		200	uA
I _{EBO}	Emitter Cutoff Current	V _{EB} =5V; I _C =0		2	mA
V _{EBO}	Emitter Cutoff Current				
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =1.5A; I _B =30mA		2.5	V
V _{CE(sat-2)}	Collector-emitter saturation voltages				
V _{CE(sat-3)}	Collector-emitter saturation voltages				
h _{FE-1}	Forward current transfer ratio	I _C =1.5A; V _{CE} =3V	750		
h _{FE-2}	Forward current transfer ratio				
V _{BE(sat-1)}	Base-Emitter Saturation Voltage				
V _{BE(sat-2)}	Base-Emitter Saturation Voltage				
f _T	Current Gain-Bandwidth Product				